

Product Summary

BV _{DSS}	R _{DS(ON)} Max	Q _g Typ	I _D T _C = +25°C (Note 9)
40V	2.7mΩ @ V _{GS} = 10V	68.6nC	100A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

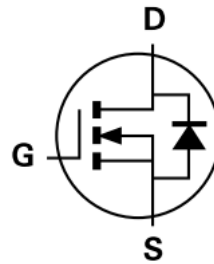
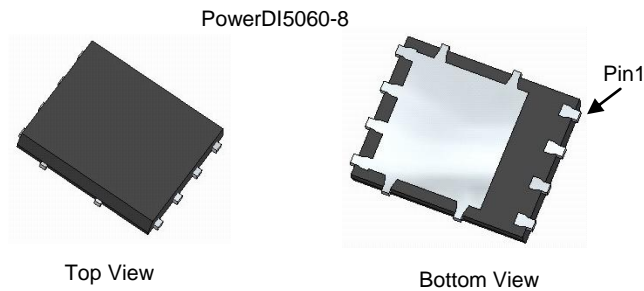
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Features

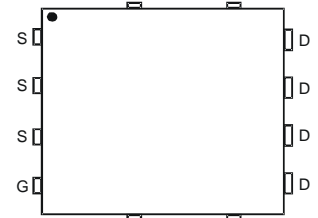
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} – Minimizes Power Losses
- Low Q_g – Minimizes Switching Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.097 grams (Approximate)



Internal Schematic



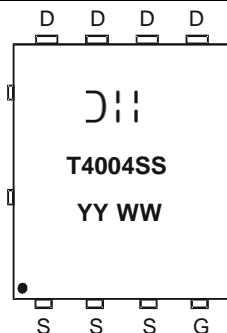
Top View Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH4004SPS-13	PowerDI5060-8	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



D = Manufacturer's Marking
 T4004SS = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 14 = 2014)
 WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	40	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 5)	I _D	T _A = +25°C	31
		T _A = +70°C	26
Continuous Drain Current (Note 6)	I _D	T _C = +25°C (Note 9)	100
		T _C = +100°C	100
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	200	A
Avalanche Current, L=0.2mH	I _{AS}	45	A
Avalanche Energy, L=0.2mH	E _{AS}	200	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	3.6	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	41	°C/W
Total Power Dissipation (Note 6)	P _D	167	W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	0.9	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 32V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	2	—	4	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	2.3	2.7	mΩ	V _{GS} = 10V, I _D = 90A
Diode Forward Voltage	V _{SD}	—	0.9	1.2	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	4,305	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	1,441	—		
Reverse Transfer Capacitance	C _{rss}	—	102	—		
Gate Resistance	R _g	—	0.77	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	68.6	—	nC	V _{DD} = 20V, I _D = 90A, V _{GS} = 10V
Gate-Source Charge	Q _{gs}	—	16.8	—		
Gate-Drain Charge	Q _{gd}	—	14.2	—		
Turn-On Delay Time	t _{D(ON)}	—	9.5	—	ns	V _{DD} = 20V, V _{GS} = 10V, I _D = 90A, R _G = 3.5Ω
Turn-On Rise Time	t _r	—	6.7	—		
Turn-Off Delay Time	t _{D(OFF)}	—	26.4	—		
Turn-Off Fall Time	t _f	—	8.1	—		
Body Diode Reverse Recovery Time	t _{RR}	—	52.4	—	ns	I _F = 50A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	78.2	—	nC	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.
 9. Package limited.

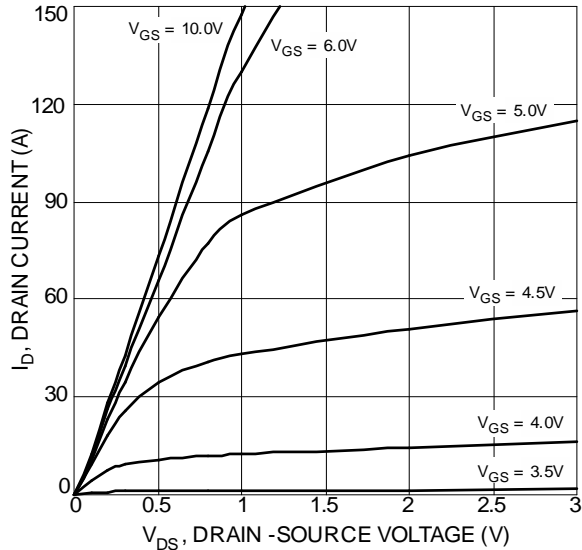


Figure 1 Typical Output Characteristics

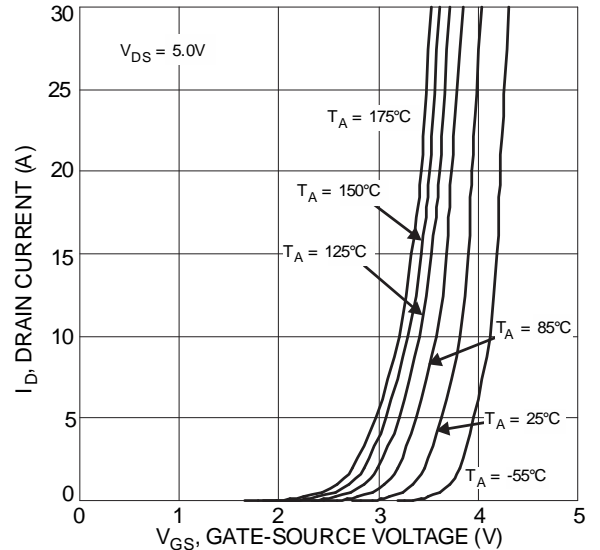


Figure 2 Typical Transfer Characteristics

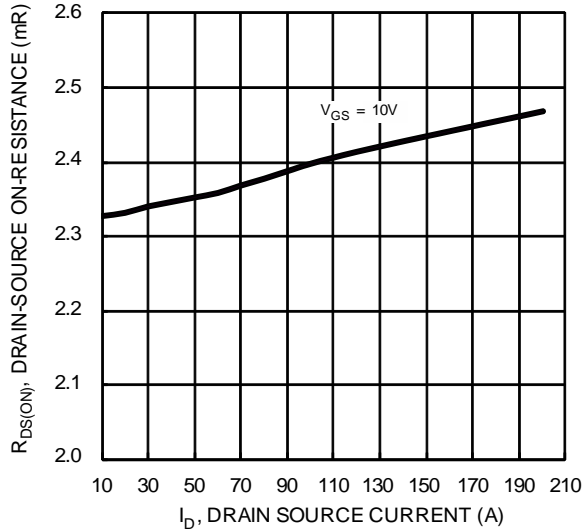


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

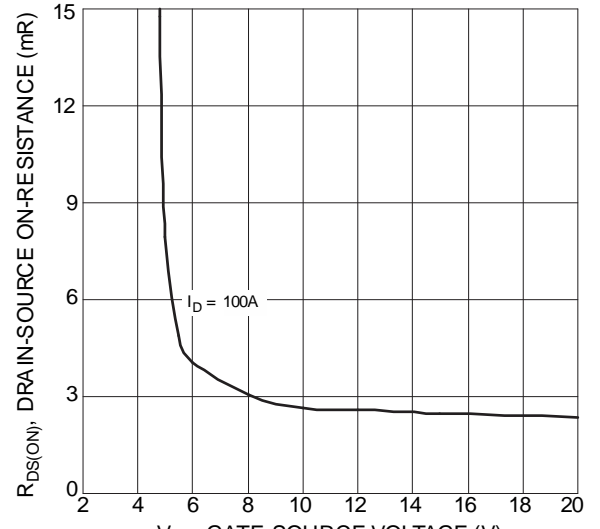


Figure 4 Typical Transfer Characteristics

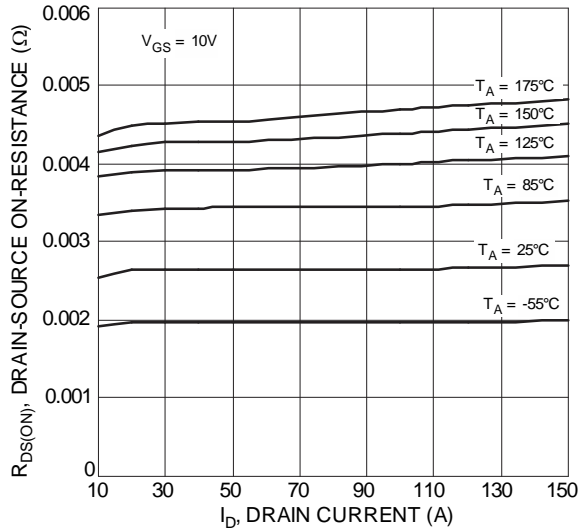


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

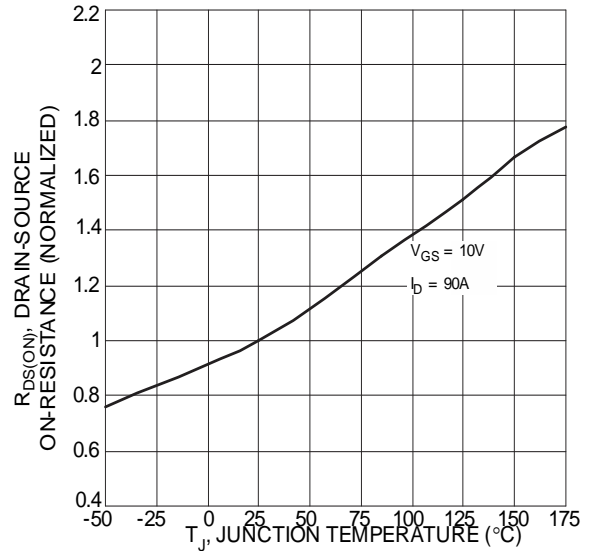


Figure 6 On-Resistance Variation with Temperature

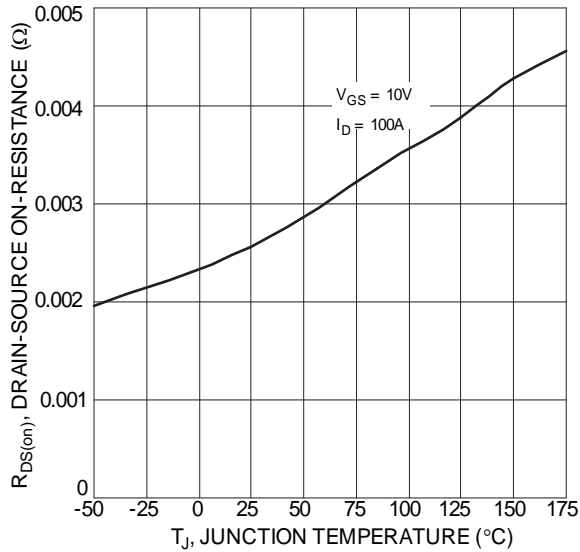


Figure 7 On-Resistance Variation with Temperature

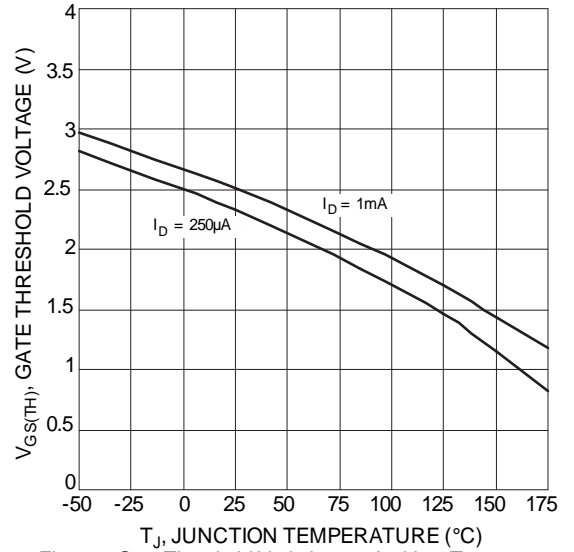


Figure 8 Gate Threshold Variation vs. Ambient Temperature

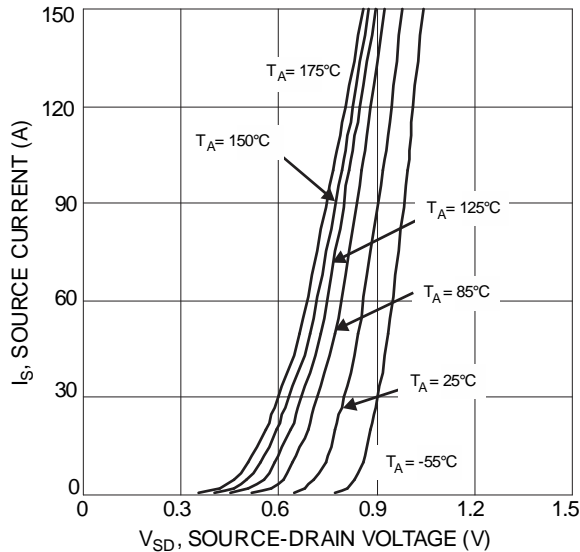


Figure 9 Diode Forward Voltage vs. Current

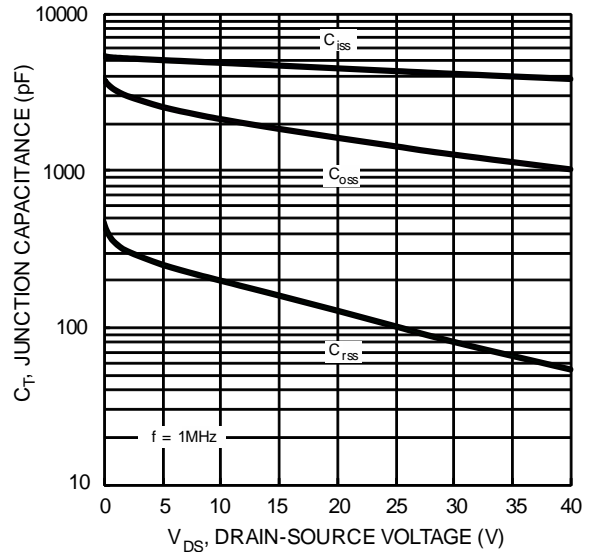


Figure 10 Typical Junction Capacitance

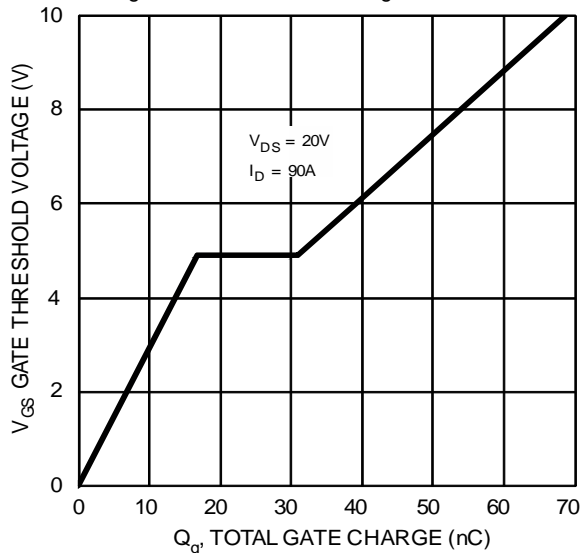


Figure 11 Gate Charge

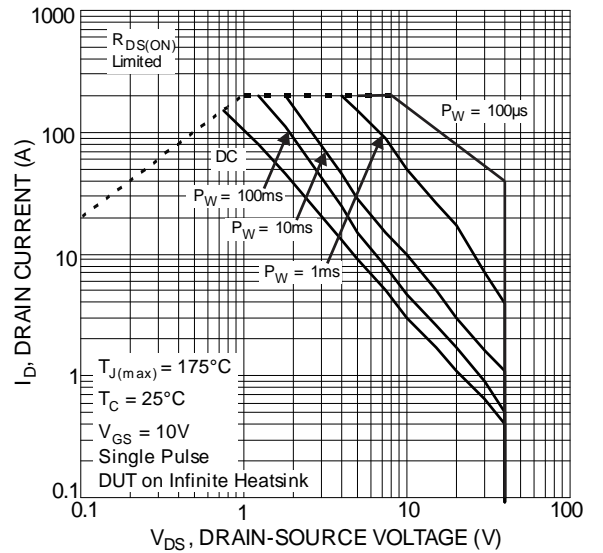
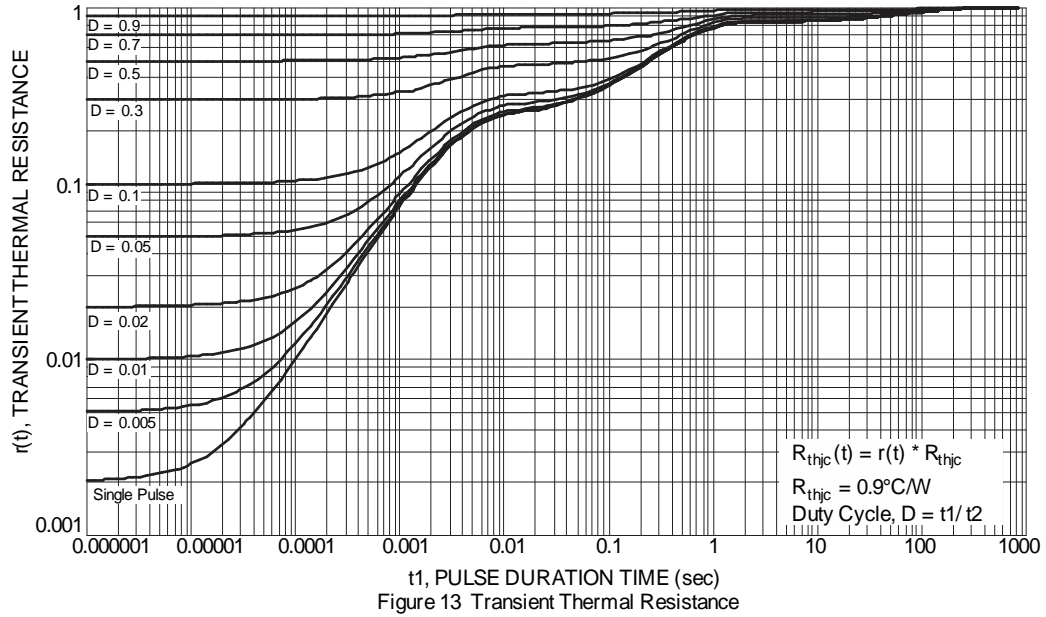


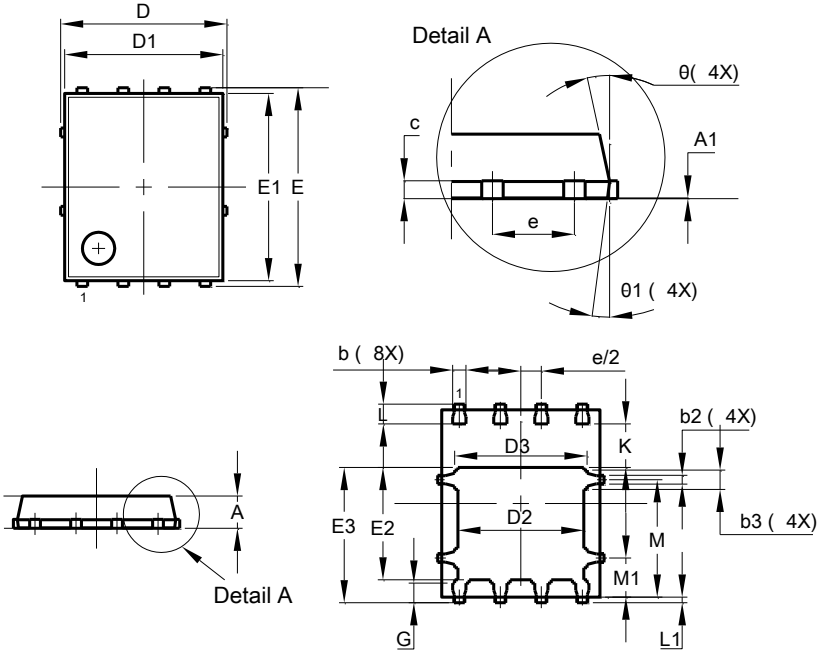
Figure 12 SOA, Safe Operation Area



Package Outline

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

PowerDI5060-8

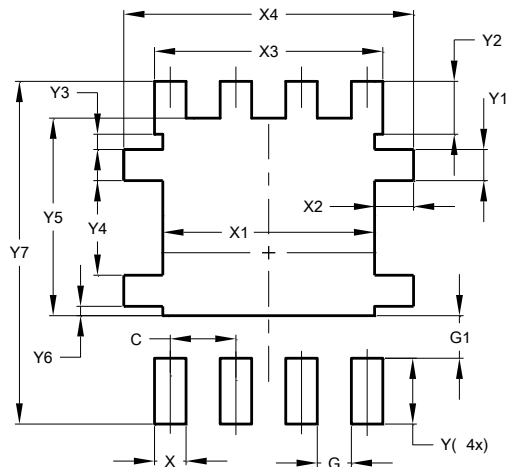


PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	-	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
theta	10°	12°	11°
theta1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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